

In the claims:

Please amend the claims as follows:

Sub J27 17. (Amended) The apparatus of claim ~~16~~¹ wherein said laser is placed outside said chamber, said chamber having a window through which said rectangular shaped laser beam having an elongated cross section is introduced into said chamber.

22 78. (Amended) The apparatus of claim ~~75~~²¹ wherein [said infrared light is irradiated to said semiconductor layer in] an atmosphere in which said semiconductor layer is placed in said light processing apparatus [containing] contains nitrogen, ammonia, nitrous oxide or oxygen.

26 79. (Amended) The apparatus of claim ~~76~~²⁵ wherein [said infrared light is irradiated to said semiconductor layer in] an atmosphere in which said semiconductor layer is placed in said light processing apparatus [containing] contains nitrogen, ammonia, nitrous oxide or oxygen.

Sub J10 80. (Amended) The apparatus of claim ~~16~~¹ wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a

silicon oxide layer formed on said semiconductor layer.

¹⁶ 81. (Amended) The apparatus of claim ¹⁰ 56 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

¹⁹ 82. (Amended) The apparatus of claim ¹⁸ 74 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

²³ 83. (Amended) The apparatus of claim ²¹ 75 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

²⁴ 84. (Amended) The apparatus of claim ²⁵ 76 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a silicon oxide layer formed on said semiconductor layer.

³⁰ 85. (Amended) The apparatus of claim ²⁹ 77 wherein [said dopant impurity is doped into] said semiconductor layer placed in said ion introducing apparatus has [through] a

~~10~~ ~~cmf.~~ silicon oxide layer formed on said semiconductor layer.

~~9~~ ~~86~~. (Amended) The apparatus of claim ~~16~~¹ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~17~~ ~~87~~. (Amended) The apparatus of claim ~~56~~¹⁰ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~20~~ ~~88~~. (Amended) The apparatus of claim ~~74~~¹⁸ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~24~~ ~~89~~. (Amended) The apparatus of claim ~~75~~²¹ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~28~~ ~~90~~. (Amended) The apparatus of claim ~~76~~²² wherein the transportation of said substrate is conducted by a [magic hand] robot arm.

~~31~~ ~~91~~. (Amended) The apparatus of claim ~~77~~²⁹ wherein the transportation of said substrate is conducted by a [magic hand] robot arm.